

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5122

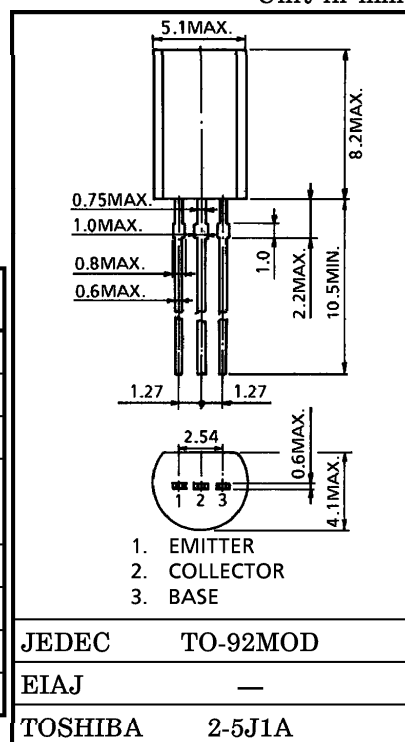
HIGH VOLTAGE SWITCHING APPLICATIONS.

Unit in mm

- High Voltage : $V_{CEO} = 400V$
- Low Saturation Voltage
: $V_{CE(sat)} = 0.4V$ (Typ.) ($I_C = 20mA, I_B = 0.5mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	DC	I_C	50
	Pulse	I_{CP}	100
Base Current	I_B	25	mA
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Weight : 0.36g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 400V, I_E = 0$	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 7V, I_C = 0$	—	—	1	μA
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	400	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 1mA$	80	—	—	
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 20mA$	100	—	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 0.5mA$	—	0.4	1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5V, I_C = 20mA$	—	0.7	1.0	V
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	4	—	pF

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